5.0V

R<sub>D</sub>=1K

K=0.75

 $mA/V^2$ 

VO

## <u>The MOSFET as an</u> <u>Amp and Switch</u>

Vτ

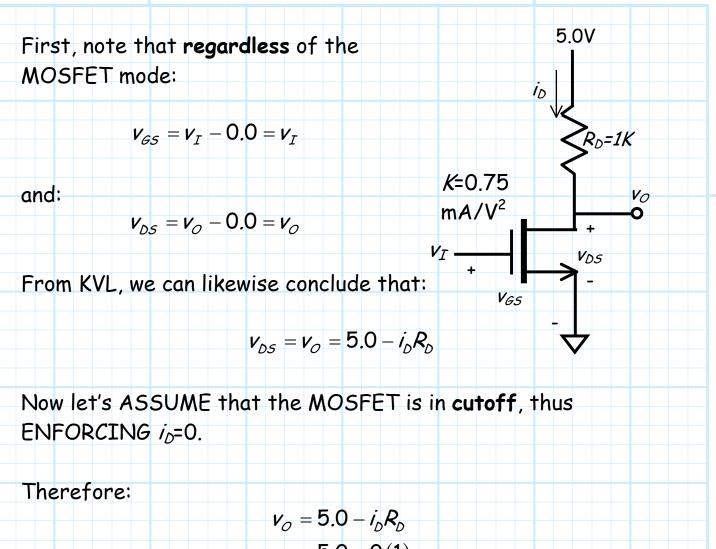
Consider this **simple** MOSFET circuit:

Q: Oh, goody—you're going to **waste** my time with another of these **pointless** academic problems. Why can't you discuss a circuit that actually **does** something?

A: Actually, this circuit is a fundamental electronic  $\nabla$  device! To see what this circuit does, we need to determine its transfer function  $v_{\mathcal{O}} = f(v_{\mathcal{I}})$ .

**Q:** Transfer function! How can we determine the transfer function of a MOSFET circuit!?

A: Same as with junction diodes—we determine the output  $v_O$  for each device mode, and then determine when (i.e., for what values of  $v_I$ ) the device is in that mode!



= 5.0 - 0(1)= 5.0 V

Now, we know that MOSFET is in cutoff when:

$$v_{GS} = v_I < V_{t} = 1.0$$

Thus, we conclude that:

 $v_{O} = 5.0 \text{ V}$  when  $v_{I} < 1.0 \text{ V}$ 

Jim Stiles

Now, let's ASSUME that the MOSFET is in **saturation**, thus ENFORCE:

$$\dot{I}_{D} = K (V_{GS} - V_{\tau})^{2}$$
  
=  $K (V_{I} - V_{\tau})^{2}$   
=  $0.75 (V_{I} - 1.0)^{2}$ 

And thus the output voltage is:

$$v_{O} = 5.0 - i_{D}R_{D}$$
  
= 5.0 - 0.75 ( $v_{I}$  - 1.0)<sup>2</sup> (1)  
= 5.0 - 0.75 ( $v_{I}$  - 1.0)<sup>2</sup>

Now, we know that MOSFET is in saturation when:

$$v_{GS} = v_I > V_t = 1.0$$

and when:

$$v_{DS} = v_{O} > v_{GS} - V_{t} = v_{I} - 1.0$$

This second inequality means:

$$v_{O} > v_{I} - 1.0$$

$$5.0 - 0.75(v_{I} - 1.0)^{2} > v_{I} - 1.0$$

$$0 > 0.75(v_{I} - 1.0)^{2} + (v_{I} - 1.0) - 5.0$$

## Solving this quadratic, we find that the only consistent solution is: $v_{I} - 1.0 < 2.0$ $v_{I} < 3.0$

Meaning that the MOSFET is in saturation when  $v_I > 1.0$  and  $v_I < 3.0$ . Logically, this is same thing as saying the MOSFET is in saturation when  $1.0 < v_I < 3.0$ .

Thus we conclude:

$$v_{O} = 5.0 - 0.75 (v_{I} - 1.0)^{2}$$
 when  $1.0 < v_{I} < 3.0$  V

Finally, let's ASSUME that the MOSFET is in **triode** mode, thus we ENFORCE:

$$i_{D} = K \left[ 2 (v_{GS} - V_{t}) v_{DS} - v_{DS}^{2} \right]$$
  
= 0.75 \left[ 2 (v\_{I} - 1.0) v\_{O} - v\_{O}^{2} \right]

And thus the output voltage is:

$$v_{O} = 5.0 - i_{D}R_{D}$$
  
= 5.0 - 0.75[2( $v_{I}$  - 1.0) $v_{O}$  -  $v_{O}^{2}$ ](1)  
= 5.0 - 0.75[2( $v_{I}$  - 1.0) $v_{O}$  -  $v_{O}^{2}$ ]

Rearranging this equation, we get the quadratic form:

$$0.75 v_{\mathcal{O}}^2 - (1.5 v_{\mathcal{I}} - 0.5) v_{\mathcal{O}} + 5.0 = 0$$

The solutions of which are:

$$v_{\mathcal{O}} = \frac{(1.5v_{\mathcal{I}} - 0.5) \pm \sqrt{(1.5v_{\mathcal{I}} - 0.5)^2 - 15.0}}{1.5}$$

Jim Stiles

Note because of the  $\pm$ , there are **two** possible solutions. However, to be in triode region, the MOSFET must not be in pinchoff, i.e.:

$$v_{O} = v_{DS} < v_{GS} - V_{t} = v_{I} - 1.0$$

This condition is satisfied with the **smaller** of the two solutions (i.e., the solution with the minus sign!):

$$v_{O} = \frac{(1.5v_{I} - 0.5) - \sqrt{(1.5v_{I} - 0.5)^{2} - 15.0}}{1.5}$$

So, the above expression provides us with the output voltage if the MOSFET is in triode mode. The question remaining is thus when (i.e., for what values of  $V_I$ ) is the MOSFET in triode mode?

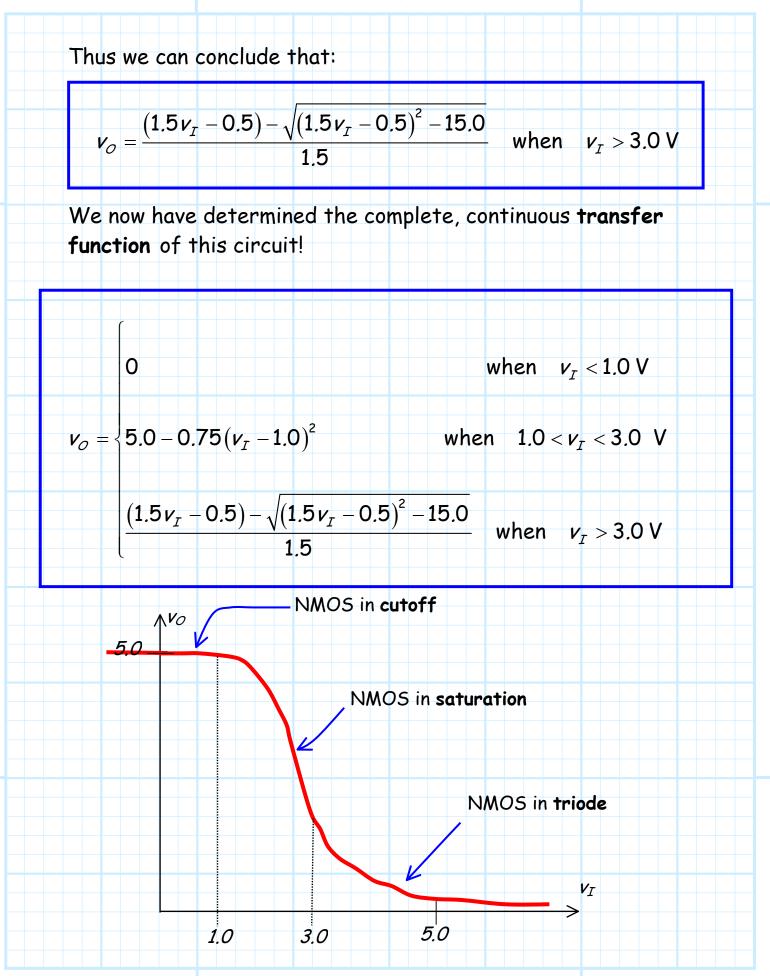
We could do a lot more math to find this answer, but this answer is actually quite **obvious**!

Recall that we have already determined that:

a) The MOSFET is in cutoff when  $v_I < 1.0$  V

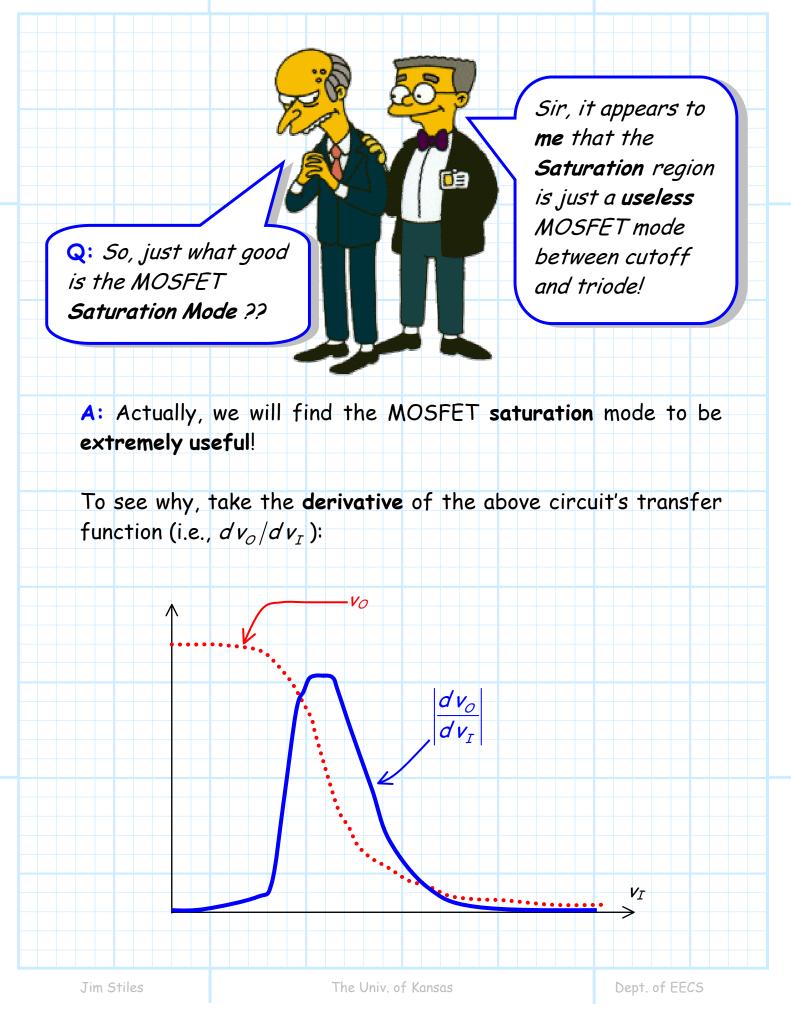
b) The MOSFET is in saturation when  $1.0 < v_T < 3.0$  V

Since there are only **three** modes of a MOSFET device, and since the transfer **function** must—well—be a **function**, we can conclude (correctly) that the MOSFET will be in triode region when  $v_I$  is the value of the **only region that is left**-- $v_I > 3.0$ !



Q: I thought you said this circuit did something. It appears to be just as pointless as all the others! A: To see how this circuit is useful, consider what happens when the input voltage  $v_I$  is 0 V and 5V. From the transfer function, we find that if  $v_T = 0$ , the output voltage will be  $v_o = 5.0$ . Likewise, if the input voltage is  $v_{I} = 5.0$ , the output voltage will be small, specifically  $v_o = 0.78 \, \text{V}$ . **∧**V0 5.0 - $V_I$ 0.78 --0.0 50 Let's summarize these results in a table:

V	ſr	Vo	Mode
0.	0	5.0	Cutoff
5.	0	small (0.78)	Triode
		this device ss at all! It i	
	•	provides a <b>sir</b> of MOSFET	•
can us	se MOS	FETs to mak OR, etc.), <b>fli</b>	ke digital de
digita `1"), t	l circuit he MOS	find that, ju is in <b>either</b> 5FETs in the v <sub>DS</sub> small) ma	of its <b>two</b> circuit will
		d <b>Triode</b> are ts and applic	



111

We note that in cutoff and triode:



 $\left|\frac{dV_{O}}{dV_{\tau}}\right| >> 1$ 

while in the saturation mode:

**Q**: Oh goody. The **slope** of the transfer function is **large** when the MOSFET is in **saturation**. Am I supposed to be impressed by that?! How are these results even **remotely** important!?

A: Since in cutoff and triode  $dv_o/dv_I = 0$ , a small change in input voltage  $v_I$  will result in almost no change in output voltage  $v_o$ .

Contrast this with the saturation region, where  $|dv_O/dv_I| >> 1$ . This means that a small change in input voltage  $v_I$  results in a large change in the output voltage  $v_O$ !

To see how this is important, consider the case where the input signal has both a **DC** and a **small-signal** (AC) component:

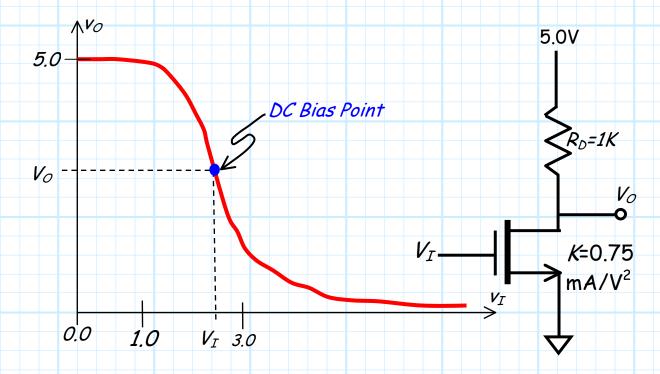
$$\boldsymbol{\nu}_{I}(\boldsymbol{t}) = \boldsymbol{\nu}_{I} + \boldsymbol{\nu}_{i}(\boldsymbol{t})$$

As a result, the **output** voltage likewise has both a DC and smallsignal component:

 $\boldsymbol{v}_{\mathcal{O}}\left(\boldsymbol{t}\right) = \boldsymbol{V}_{\mathcal{O}} + \boldsymbol{v}_{o}\left(\boldsymbol{t}\right)$ 

Now, let's consider **only** the **DC** components. We can select the DC input  $V_I$  such that the MOSFET is placed in **saturation**. The value  $V_I$ , along with the resulting DC output  $V_O$ , sets a **DC bias point** for this circuit.

By selecting the right value of  $V_I$  we **could** set this DC bias point to where the transfer function **slope** is the greatest:



Now, say we add a small-signal  $v_i$  to this input DC voltage (i.e.,  $v_I(t) = V_I + v_i(t)$ ). This small signal simply represents a small change in the input voltage from its average (i.e., DC) value. The result is of course as small change in the output voltage the small-signal output voltage  $v_o(t)$ ! Now for the **interesting** part (I bet you were wondering when I would get around to it)! The small change in the output voltage will have a much **larger** magnitude than the small change in the input!

For example, if the input voltage changes by **1** mV (i.e.,  $v_i = 1$ mV), the output **might** change by, say, **5** mV (i.e.,  $v_o = 5$  mV).

Q: Goodness! By how much would the **output** change in our example circuit? How can we **determine** the smallsignal **output** v<sub>o</sub> ??

Determining how much the output voltage of our circuit will change when we change the input voltage by a small amount is very **straightforward**—we simply take the **derivative** of the output voltage  $v_0$  with respect to input voltage  $v_1$ !

By taking the **derivative** of  $v_0$  with respect to  $v_I$  (when the MOSFET is in saturation, we find:

$$\frac{d v_{O}}{dv_{I}} = \frac{d \left(5.0 - 0.75 \left(v_{I} - 1.0\right)^{2}\right)}{dv_{I}}$$
$$= -1.50 \left(v_{I} - 1.0\right) \qquad \text{for} \quad 1.0 < v_{I} < 3.0$$

This expression describes the **slope** of our circuit's transfer function (for  $1.0 < v_I < 3.0$ ). Note the slope with the **largest magnitude** occurs when  $v_I = 3.0$ , providing a **slope** of -3.0 mV/mV.

13/14

Thus, **if** we DC bias this circuit with  $V_I = 3.0$  V (resulting in  $V_O = 2.0$  V), we find that the small signal output will be **3 times** the small signal input!

For example, say that the **input** to our circuit is:

$$v_{\tau} = 3.0 + 0.01 \cos \omega t$$
 V

(i.e.,  $V_I = 3.0$  V and  $v_i = 0.01 \cos \omega t$ ). We would find that the **output voltage** would approximately be:

$$v_{o} = 2.0 - 0.03 \cos \omega t$$
 V

(i.e.,  $V_I = 2.0$  V and  $v_o = -0.03 \cos \omega t$ ). Note then that:

$$v_o = \frac{d'v_o}{dv_I} \bigg|_{v_I=3.0} v_i$$
$$= -3.0 v_i$$
$$= -0.03 \cos \omega t$$

In other words, the magnitude of the small-signal output has a magnitude **three times larger** than the input magnitude.

We say then that our signal provides small-signal gain—our circuit is also a small-signal amplifier!

I see. A **small** voltage change results in a **big** voltage change—it's **voltage gain**!

The **MOSFET saturation** mode turns out to be—**excellent**.



Even the simple circuit of this example is sufficient demonstrates to demonstrate the **two primary applications** of MOSFET transistors--**digital** circuits and signal **amplification**.

Whereas the important MOSFET regions for **digital** devices are **triode** and **cutoff**, MOSFETs in amplifier circuits are typically biased into the **saturation** mode!